

Vorläufige Daten
preliminary data

IGBT-Wechselrichter / IGBT-inverter

Höchstzulässige Werte / maximum rated values

Kollektor-Emitter-Sperrspannung collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}$	$I_{C\text{ nom}}$ I_C	10 16	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_P = 1\text{ ms}$, $T_C = 80^{\circ}\text{C}$	I_{CRM}	20	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^{\circ}\text{C}$	P_{tot}	78,0	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / characteristic values

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 10\text{ A}$, $V_{GE} = 15\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$ $I_C = 10\text{ A}$, $V_{GE} = 15\text{ V}$, $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{ sat}}$		1,90 2,20	2,45	V V
Gate-Schwellenspannung gate threshold voltage	$I_C = 0,30\text{ mA}$, $V_{CE} = V_{GE}$, $T_{vj} = 25^{\circ}\text{C}$	V_{GEth}	5,0	5,8	6,5	V
Gateladung gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$	Q_G		0,10		μC
Interner Gatewiderstand internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$	R_{Gint}		0,0		Ω
Eingangskapazität input capacitance	$f = 1\text{ MHz}$, $T_{vj} = 25^{\circ}\text{C}$, $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$	C_{ies}		0,70		nF
Rückwirkungskapazität reverse transfer capacitance	$f = 1\text{ MHz}$, $T_{vj} = 25^{\circ}\text{C}$, $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$	C_{res}		0,026		nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 1200\text{ V}$, $V_{GE} = 0\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$	I_{CES}			5,0	mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$	I_{GES}			400	nA
Einschaltverzögerungszeit (ind. Last) turn-on delay time (inductive load)	$I_C = 10\text{ A}$, $V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 82\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 82\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{ on}}$		0,05 0,05		μs μs
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 10\text{ A}$, $V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 82\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 82\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	t_r		0,02 0,025		μs μs
Abschaltverzögerungszeit (ind. Last) turn-off delay time (inductive load)	$I_C = 10\text{ A}$, $V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 82\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 82\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{ off}}$		0,23 0,35		μs μs
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 10\text{ A}$, $V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 82\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 82\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	t_f		0,09 0,15		μs μs
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 10\text{ A}$, $V_{CE} = 600\text{ V}$, $L_S = 70\text{ nH}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 82\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 82\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	E_{on}		0,75 1,20		mJ mJ
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 10\text{ A}$, $V_{CE} = 600\text{ V}$, $L_S = 70\text{ nH}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 82\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 82\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	E_{off}		0,75 1,10		mJ mJ
Kurzschlußverhalten SC data	$t_P \leq 10\ \mu\text{s}$, $V_{GE} \leq 15\text{ V}$ $T_{vj} \leq 125^{\circ}\text{C}$, $V_{CC} = 900\text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	I_{sc}		35		A
Innerer Wärmewiderstand thermal resistance, junction to case	pro IGBT per IGBT	R_{thJC}		1,60	1,80	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		0,45		K/W

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Diode-Wechselrichter / diode-inverter

Höchstzulässige Werte / maximum rated values

Periodische Spitzensperrspannung repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Dauergleichstrom DC forward current		I_F	10	A
Periodischer Spitzenstrom repetitive peak forward current	$t_P = 1 \text{ ms}$	I_{FRM}	20	A
Grenzlastintegral I^2t - value	$V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	40,0	A ² s

Charakteristische Werte / characteristic values

			min.	typ.	max.	
Durchlassspannung forward voltage	$I_F = 10 \text{ A}, V_{GE} = 0 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $I_F = 10 \text{ A}, V_{GE} = 0 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	V_F		1,65 1,65	2,10	V V
Rückstromspitze peak reverse recovery current	$I_F = 10 \text{ A}, -di_F/dt = 600 \text{ A}/\mu\text{s}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	I_{RM}		20,0 19,0		A A
Sperrverzögerungsladung recovered charge	$I_F = 10 \text{ A}, -di_F/dt = 600 \text{ A}/\mu\text{s}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	Q_r		1,10 2,10		μC μC
Abschaltenergie pro Puls reverse recovery energy	$I_F = 10 \text{ A}, -di_F/dt = 600 \text{ A}/\mu\text{s}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	E_{rec}		0,40 0,75		mJ mJ
Innerer Wärmewiderstand thermal resistance, junction to case	pro Diode per diode	R_{thJC}		1,90	2,10	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		0,60		K/W

NTC-Widerstand / NTC-thermistor

Charakteristische Werte / characteristic values

			min.	typ.	max.	
Nennwiderstand rated resistance	$T_C = 25^{\circ}\text{C}$	R_{25}		5,00		k Ω
Abweichung von R_{100} deviation of R_{100}	$T_C = 100^{\circ}\text{C}, R_{100} = 493 \Omega$	$\Delta R/R$	-5		5	%
Verlustleistung power dissipation	$T_C = 25^{\circ}\text{C}$	P_{25}			20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298, 15\text{K}))]$	$B_{25/50}$		3375		K

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Technische Information / technical information

IGBT-Module
IGBT-modules

FS10R12YT3



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Modul / module

Isolations-Prüfspannung insulation test voltage	RMS, f = 50 Hz, t = 1 min	V _{ISO}	2,5	kV
Material für innere Isolation material for internal insulation			Al ₂ O ₃	
Kriechstrecke creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		13,5 7,50	mm
Luftstrecke clearance distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		12,0 7,50	mm
Vergleichszahl der Kriechwegbildung comparative tracking index		CTI	> 225	
			min. typ. max.	
Modulinduktivität stray inductance module		L _{sCE}	35	nH
Modulleitungswiderstand, Anschlüsse - Chip module lead resistance, terminals - chip	T _C = 25°C, pro Zweig / per arm	R _{CC+EE'}	4,00	mΩ
Höchstzulässige Sperrschichttemperatur maximum junction temperature		T _{vj max}	150	°C
Temperatur im Schaltbetrieb temperature under switching conditions		T _{vj op}	-40	125 °C
Lagertemperatur storage temperature		T _{stg}	-40	125 °C
Anpreßkraft für mech. Bef. pro Feder mounting force per clamp		F	40	- 80 N
Gewicht weight		G	36	g

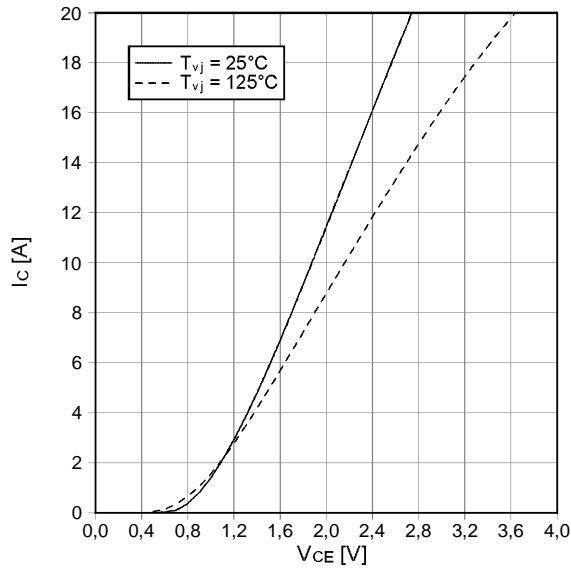
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This technical information specifies semiconductor devices but guarantees no characteristics. It is valid with the appropriate technical explanations.

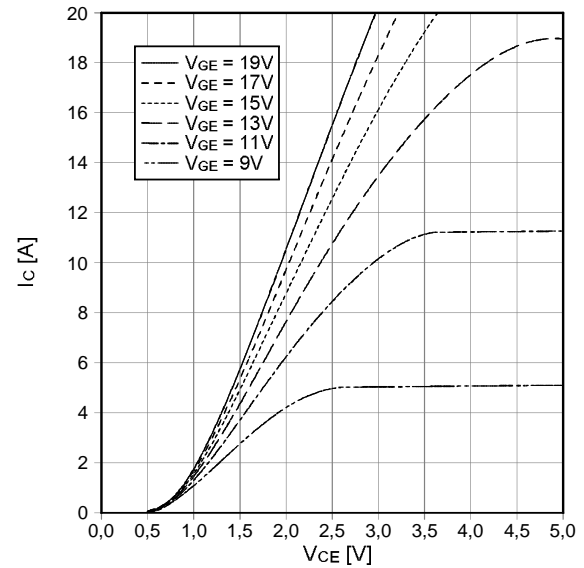
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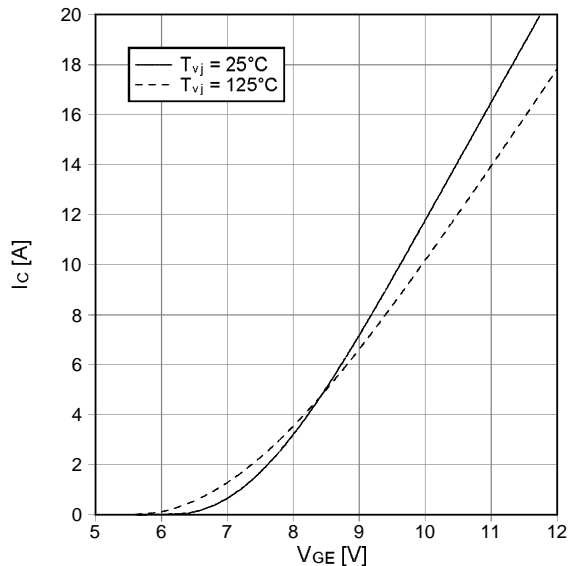
Ausgangskennlinie IGBT-Wechselr. (typisch)
output characteristic IGBT-inverter (typical)
 $I_c = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



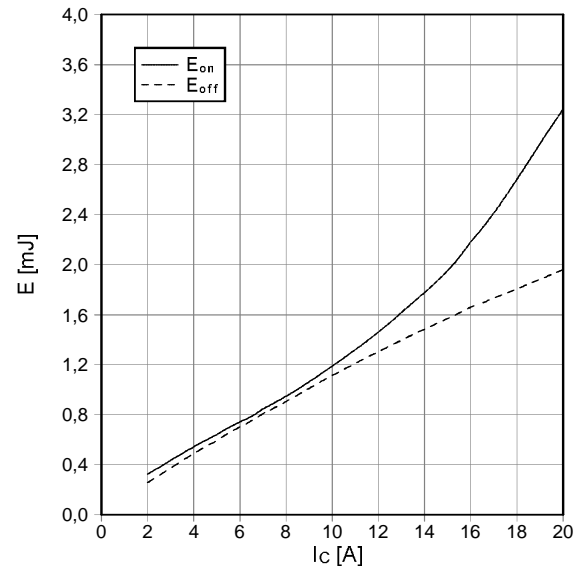
Ausgangskennlinienfeld IGBT-Wechselr. (typisch)
output characteristic IGBT-inverter (typical)
 $I_c = f(V_{CE})$
 $T_{vj} = 125^\circ\text{C}$



Übertragungscharakteristik IGBT-Wechselr. (typisch)
transfer characteristic IGBT-inverter (typical)
 $I_c = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



Schaltverluste IGBT-Wechselr. (typisch)
switching losses IGBT-inverter (typical)
 $E_{on} = f(I_c), E_{off} = f(I_c)$
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 82\ \Omega, R_{Goff} = 82\ \Omega, V_{CE} = 600\text{ V},$
 $T_{vj} = 125^\circ\text{C}$

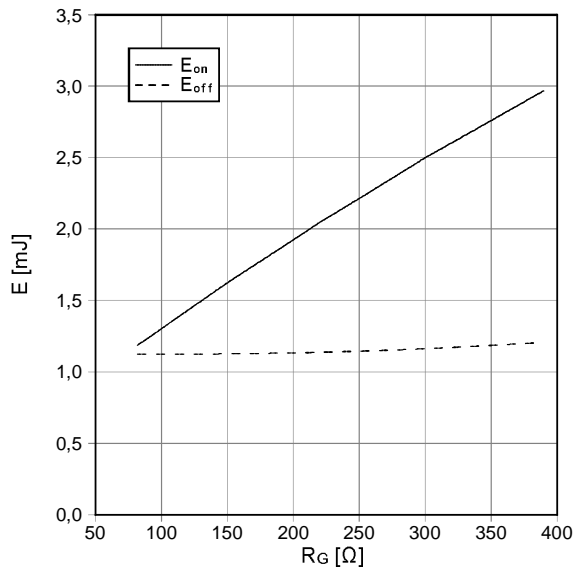


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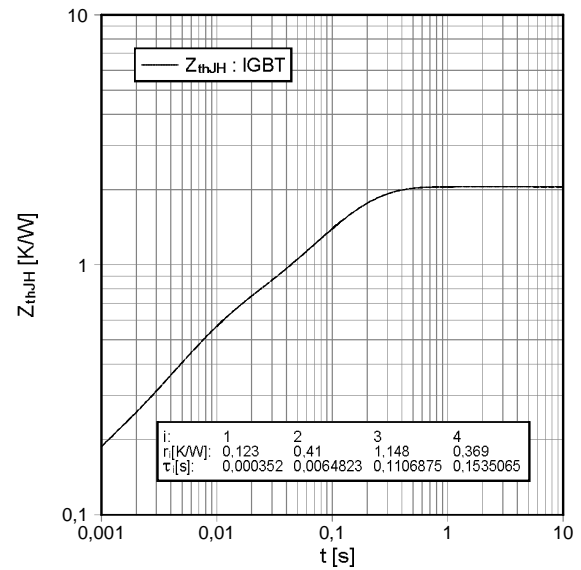
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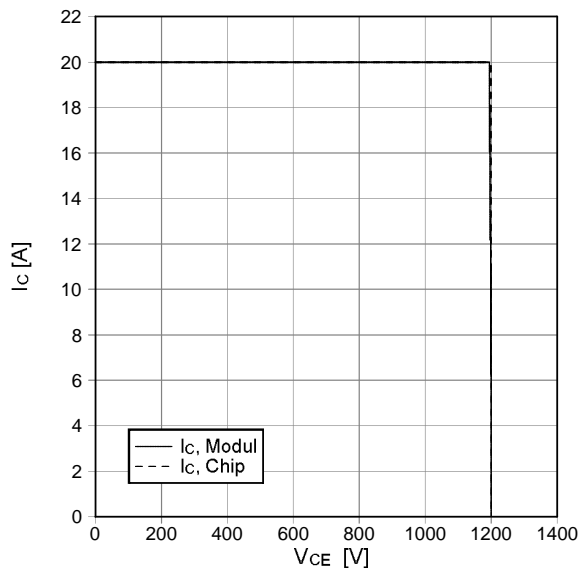
Schaltverluste IGBT-Wechselr. (typisch)
switching losses IGBT-Inverter (typical)
 $E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 10\text{ A}$, $V_{CE} = 600\text{ V}$, $T_{vj} = 125^\circ\text{C}$



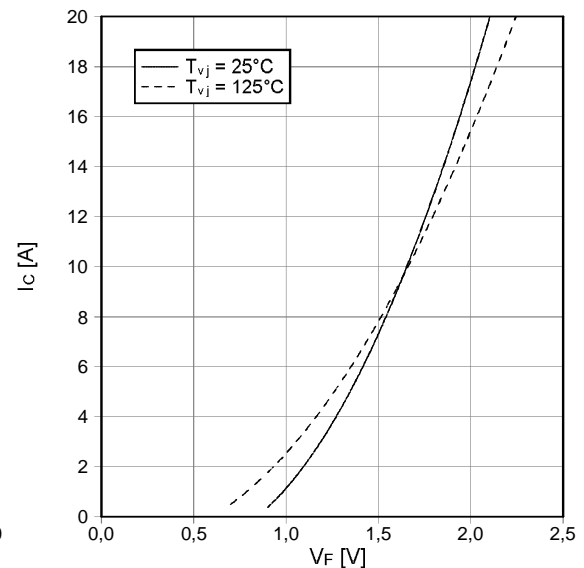
Transienter Wärmewiderstand IGBT-Wechselr.
transient thermal impedance IGBT-inverter
 $Z_{thJH} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT-Wr. (RBSOA)
reverse bias safe operating area IGBT-inv. (RBSOA)
 $I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 82\ \Omega$, $T_{vj} = 125^\circ\text{C}$



Durchlaßkennlinie der Diode-Wechselr. (typisch)
forward characteristic of diode-inverter (typical)
 $I_F = f(V_F)$

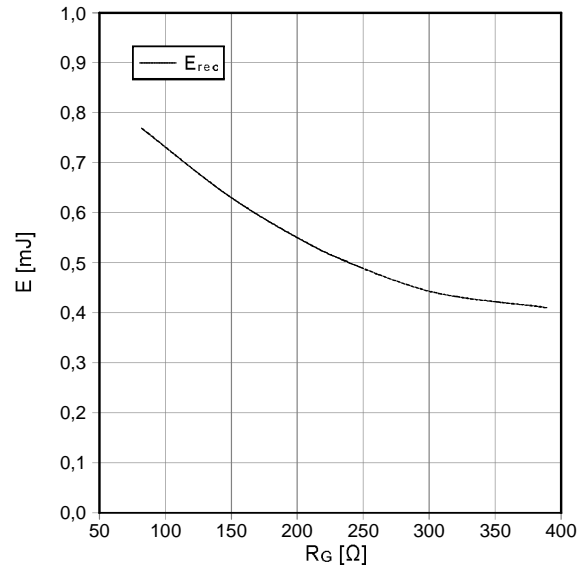
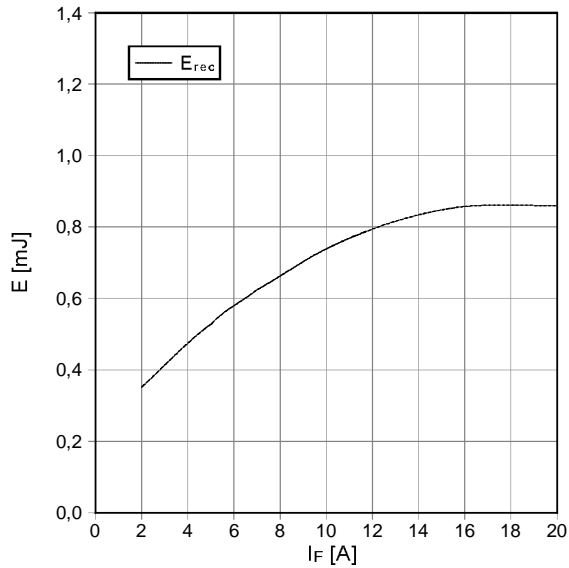


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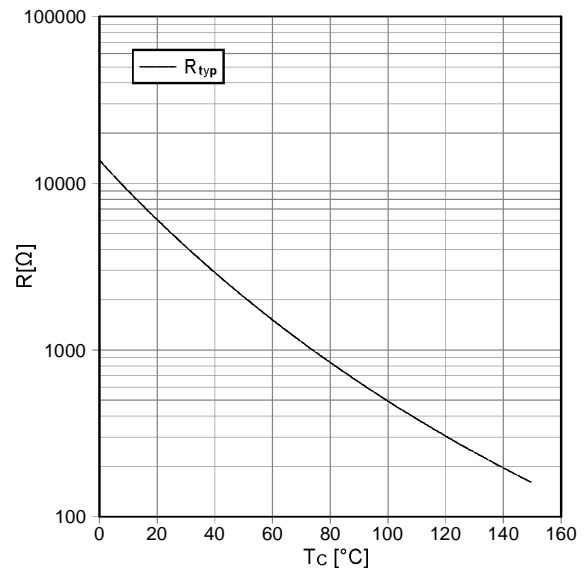
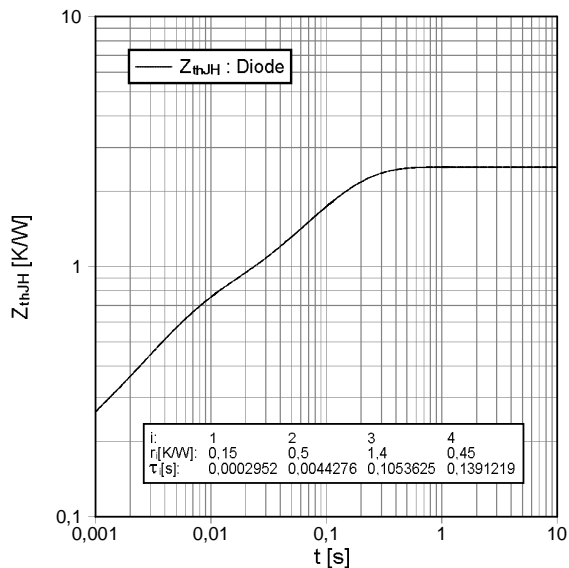
Schaltverluste Diode-Wechselr. (typisch)
switching losses diode-inverter (typical)
 $E_{rec} = f(I_F)$
 $R_{Gon} = 82 \Omega$, $V_{CE} = 600 V$, $T_{vj} = 125^\circ C$

Schaltverluste Diode-Wechselr. (typisch)
switching losses diode-inverter (typical)
 $E_{rec} = f(R_G)$
 $I_F = 10 A$, $V_{CE} = 600 V$, $T_{vj} = 125^\circ C$



Transienter Wärmewiderstand Diode-Wechselr.
transient thermal impedance diode-inverter
 $Z_{thjH} = f(t)$

NTC-Temperaturkennlinie (typisch)
NTC-temperature characteristic (typical)
 $R = f(T)$



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